

TENTATIVE

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

HN3C14FT

VHF~UHF BAND LOW NOISE AMPLIFIER APPLICATIONS

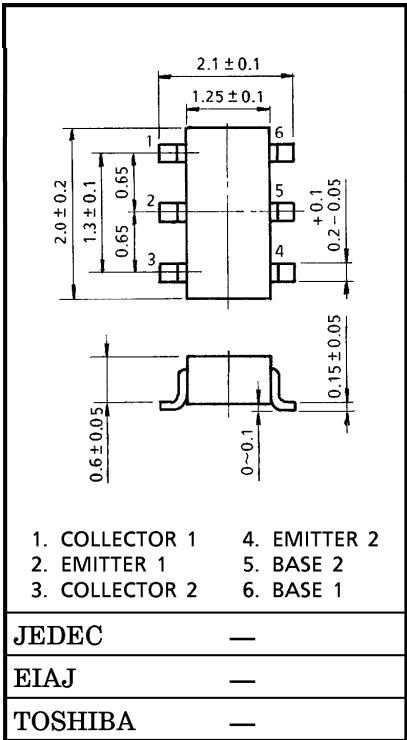
- TWO devices are built in to the super-thin and ultra super mini (6pins) package : TU6

MOUNTED DEVICES

	Q1 / Q2
Three-pins (SSM) mold products are corresponded	2SC5111

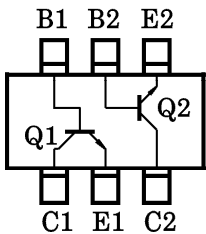
MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	VCBO	20	V
Collector-Emitter Voltage	VCEO	10	V
Emitter-Base Voltage	VEBO	3	V
Collector Current	IC	60	mA
Base Current	IB	30	mA
Collector Power Dissipation	PC	200	mW
Junction Temperature	Tj	125	°C
Storage Temperature Range	Tstg	-55~125	°C

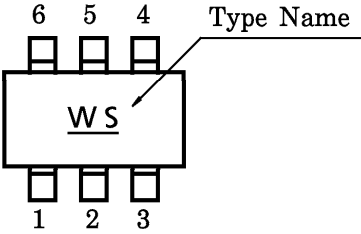


Weight : 0.008g

PIN ASSIGNMENT (TOP VIEW)



MARKING



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ELECTRICAL CHARACTERISTICS (Q1, Q2) (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 10V, I_E = 0$	—	—	1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 1V, I_C = 0$	—	—	1	μA
DC Current Gain	h_{FE}	$V_{CE} = 5V, I_C = 5mA$	80	—	240	—
Transition Frequency	f_T	$V_{CE} = 5V, I_C = 5mA$	3	5	—	GHz
Insertion Gain	$ S_{21e} ^2$	$V_{CE} = 5V, I_C = 5mA,$ $f = 1000MHz$	6	10	—	dB
Output Capacitance	C_{ob}	$V_{CB} = 5V, I_E = 0, f = 1MHz$ (Note)	—	0.9	—	pF
Reverse Transfer Capacitance	C_{re}		—	0.7	—	pF
Collector-Base Time Constant	$C_c \cdot r_{bb}'$	$V_{CB} = 5V, I_C = 3mA, f = 30MHz$	—	6	11	ps

(Note) C_{re} is measured by 3 terminal method capacitance bridge.